

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SD553

HIGH CURRENT SWITCHING APPLICATIONS

POWER AMPLIFIER APPLICATIONS

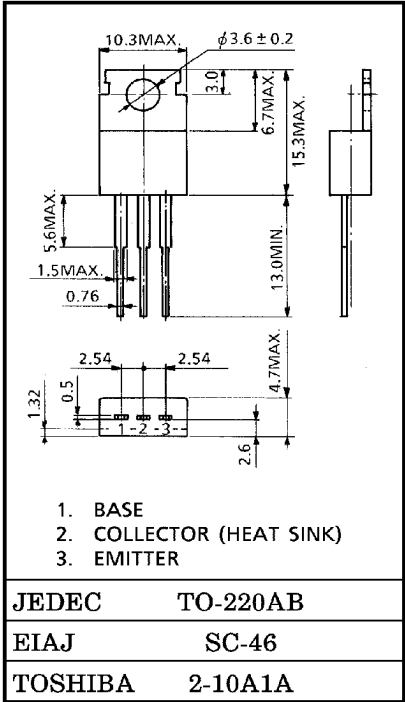
- Low Saturation Voltage : $V_{CE(sat)}=0.4V$ (Max.) (at $I_C=4A$)
- Complementary to 2SB553.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	70	V
Collector-Emitter Voltage		V_{CEO}	50	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current		I_C	7	A
Base Current		I_B	1	A
Collector Power Dissipation	Ta = 25°C	P_C	1.5	W
	Tc = 25°C		40	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

INDUSTRIAL APPLICATIONS

Unit in mm

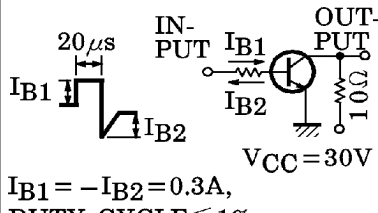


Weight : 1.9g
Mounting Kit No. AC75

961001EAA2

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} = 70V, I _E = 0	—	—	30	μA
Emitter Cut-off Current		IEBO	V _{EB} = 5V, I _C = 0	—	—	50	μA
Collector-Emitter Breakdown Voltage		V _(BR) CEO	I _C = 50mA, I _B = 0	50	—	—	V
DC Current Gain	h _{FE} (1) (Note)		V _{CE} = 1V, I _C = 1A	70	—	240	
	h _{FE} (2)		V _{CE} = 1V, I _C = 4A	30	—	—	
Collector-Emitter Saturation Voltage		V _{CE} (sat)	I _C = 4A, I _B = 0.4A	—	0.2	0.4	V
Base-Emitter Saturation Voltage		V _{BE} (sat)	I _C = 4A, I _B = 0.4A	—	0.9	1.2	V
Transition Frequency		f _T	V _{CE} = 4V, I _C = 1A	—	10	—	MHz
Collector Output Capacitance		C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	250	—	pF
Switching Time	Turn-on Time	t _{on}	 IN-PUT I _{B1} I _{B2} OUT-PUT V _{CC} = 30V	—	0.2	—	μs
	Storage Time	t _{stg}		—	2.5	—	
	Fall Time	t _f		—	0.5	—	

Note : h_{FE} (1) Classification O : 70~140, Y : 120~240

